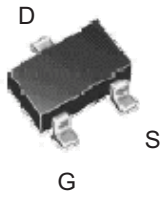
N-Channel Enhancement Mode Field Effect Transistor

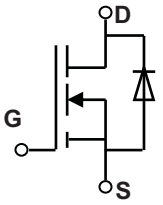
FEATURES

- Super high dense cell design for low $R_{DS(ON)}$
- Rugged and reliable
- Simple drive requirement
- SOT-23 package

PRODUCT SUMMARY		
V_{DSS}	I_D	$R_{DS(ON)}$ (mΩ) Typ
20V	4.0A	46 @ V_{GS}=10V
		65@ V_{GS}=4.5V

NOTE：The MT2306 is available in a lead-free package





ABSOLUTE MAXIMUM RATINGS（T_A=25℃ unless otherwise noted）

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	20	V
Gate-Source Voltage	V_{GS}	12	V
Drain Current-Continuous[a] @Tj=125℃	I_D	4.0	A
- Pulse [b]	I_{DM}	10	A
Drain-source Diode Forward Current[a]	I_S	1.25	A
Maximum Power Dissipation[a]	P_D	1.25	W
Operating Junction and Storage Temperature Range	T_J,T_{STG}	-55 to 150	℃

THERMAL CHARACTERISTICS

Thermal Resistance, Junction-to Ambient[a]	Rth J_A	100	℃/W

ELECTRICAL CHARACTERISTICS (T_A=25℃ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V,I_D=250μA	20			V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=16V,V_{GS}=0V			1	μA
Gate-Body Leakage	I_{GSS}	V_{GS}=±8V,V_{DS}=0V			±100	nA
ON CHARACTERITICS						
Gate Threshold Voltage	V_{GS}(th)	V_{DS}=V_{GS},I_D=250μA	0.5	0.8	1.5	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	V_{GS}=4.5V,I_D=2.8A		46	55	mΩ
		V_{GS}=2.5V,I_D=2.0A		65	76	
Forward Transconductance	g_{FS}	V_{GS}=7V,I_D=5A		5		S
DAYNAMIC CHARACTERISTICS						
Input Capacitance	C_{ISS}	V_{DS}=10V,V_{GS}=0V f=1.0MHz		608		pF
Output Capacitance	C_{OSS}			115		pF
Reverse Transfer Capacitance	C_{RSS}			86		pF
SWITCHING CHARACTERISISTICS						
Turn-On Delay Time	$t_{D(ON)}$	V_{DD}=10V I_D=3.6A, V_{GEN}=4.5V R_L=10ohm R_{GEN}=10ohm		10		ns
Rise Time	tr			14		ns
Turn-Off Delay Time	$t_{D(OFF)}$			39		ns
Fall Time	tf			26		ns
Total Gate Charge	Qg	V_{DS}=10V,I_D=1A V_{GS}=4.5V		9.2		nC
Gate-Source Charge	Qgs			1.6		nC
Gate-Drain Charge	Qgd			2.6		nC

ELECTRICAL CHARACTERICS (TA=25℃ unless otherwise noted)

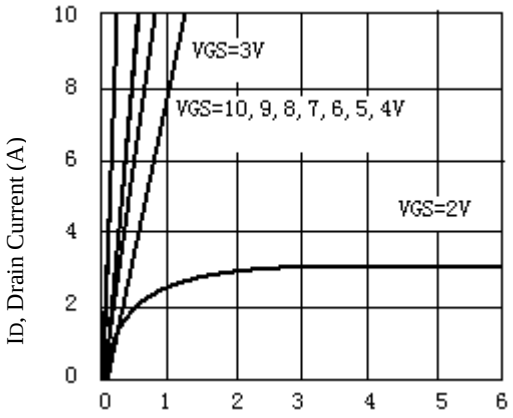
Parameter	Symbol	Condition	Min	Typ	Max	Unit
DRAIN-SOURCE DIODE CHARACTERISTICS						
Diode Forward Voltage	V_{SD}	V_{GS}=0V,I_S=1.25A		0.84	1.3	V

Notes

a. Surface Mounted on FR4 Board, t≦10sec

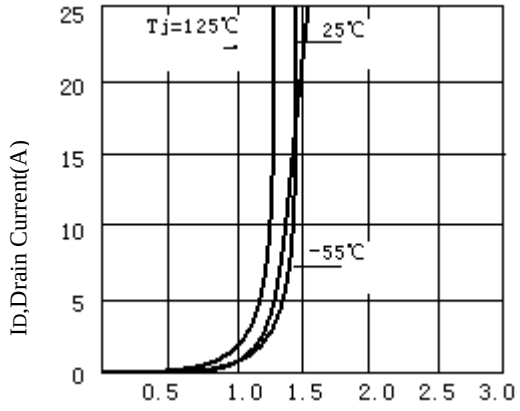
b. Pulse Test: Pulse Width≦300Us, Duty Cycle≦2%

c. Guaranteed by design, not subject to production testing.



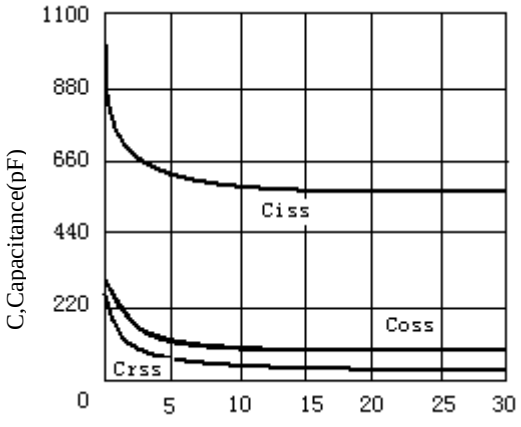
V_{DS}, Drain-to-Source Voltage (V)

Figure 1. Output Characteristics



V_{GS}, Gate-to-source Voltage (V)

Figure 2. Transfer Characteristics



VGS, Drain-to Source Voltage

Figure3. Capacitance

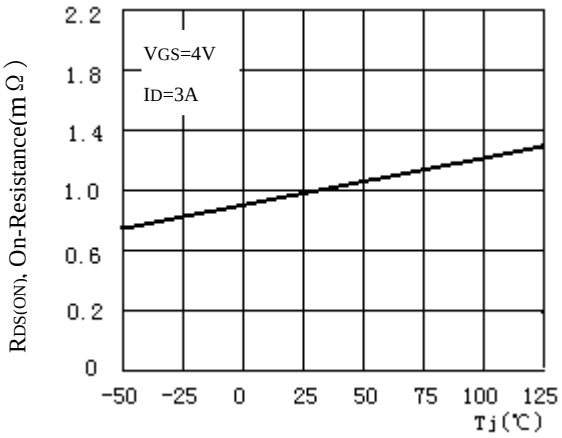


Figure4. On-Resistance Variation with Temperature

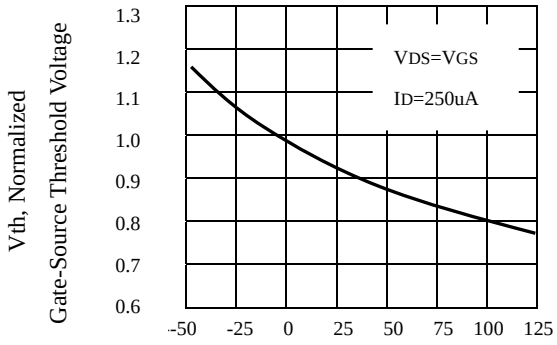


Figure5.Gate Threshold Variation With Temperature

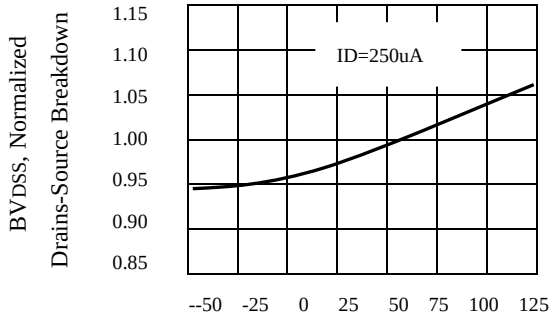


Figure6.Breakdown Voltage Variation With Temperature

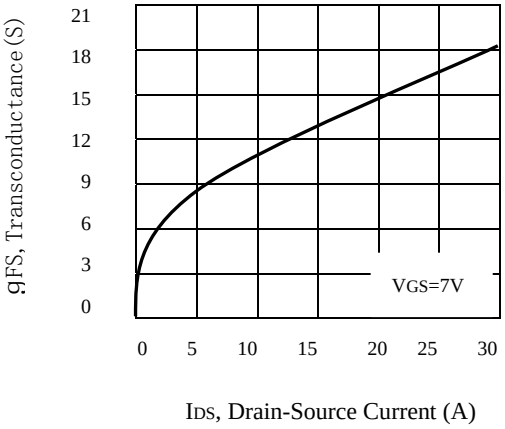


Figure7.Transconductance Variation With Drain Current

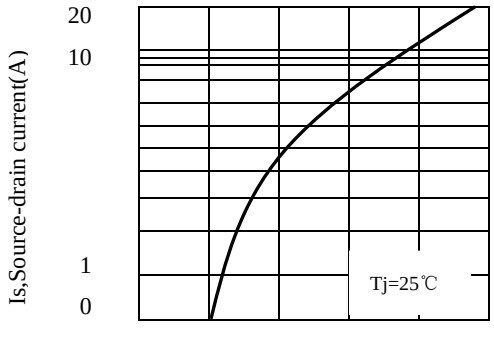


Figure8.Body Diode Forward Voltage Variation with Source Current

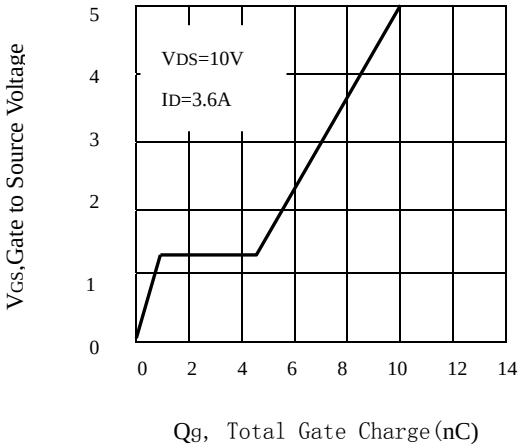


Figure9. Gate Charge

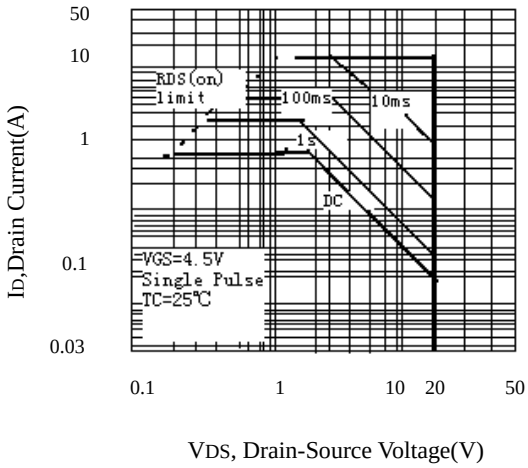


Figure10.Maximum Safe Operating Area

SOT-23 Std Tape and Reel Data

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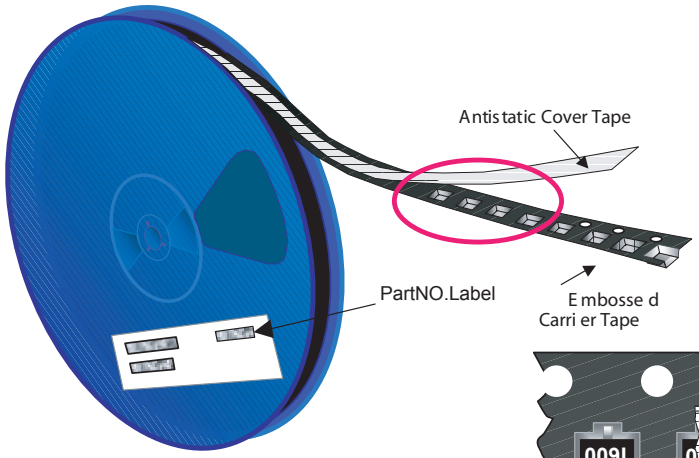
SOT23-3L Packaging
Configuration: Figure 1.0

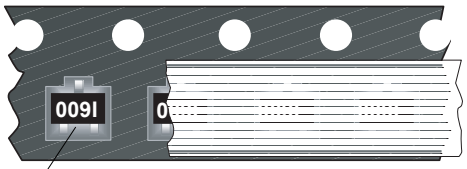


Packaging Description:

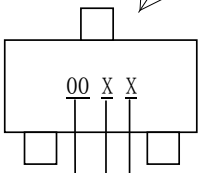
SOT23-3L parts are shipped in tape. The carrier tape is made from a dissipative (carbon filled) polycarbonate resin. The cover tape is a multilayer film (Heat Activated Adhesive in nature) primarily composed of polyester film, adhesive layer, sealant, and anti-static sprayed agent. These reeled parts in standard option are shipped with 3,000 units per 7" or 177mm diameter reel. The reels are dark blue in color and is made of polystyrene plastic (anti-static coated). Other option comes in 10,000 units per 13" or 330cm diameter reel. This and some other options are described in the Packaging Information table.

These full reels are individually labeled and placed inside a standard immediate box made of recyclable corrugated brown paper with a Fairchild logo printing. One box contains five reels maximum. And these immediate boxes are placed inside a labeled shipping box which comes in different sizes depending on the number of parts shipped.

SOT23-3L Packaging Information		
Packaging Option	Standard (no flow code)	D87Z
Packaging type	TNR	TNR
Qty per Reel/Tube/Bag	3,000	10,000
Reel Size	7" Dia	13"
Box Dimension (mm)	193x183x80	355x333x40
Max qty per Box	15,000	30,000
Weight per unit (gm)	0.0082	0.0082
Weight per Reel (kg)	0.1175	0.4006
Note/Comments		

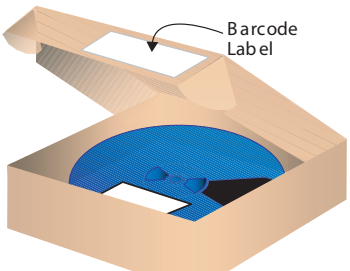


SOT23-3L Unit Orientation



MARKING DIAGRAM

X:Month Code
X:Year Code
00：Manufacturer ID

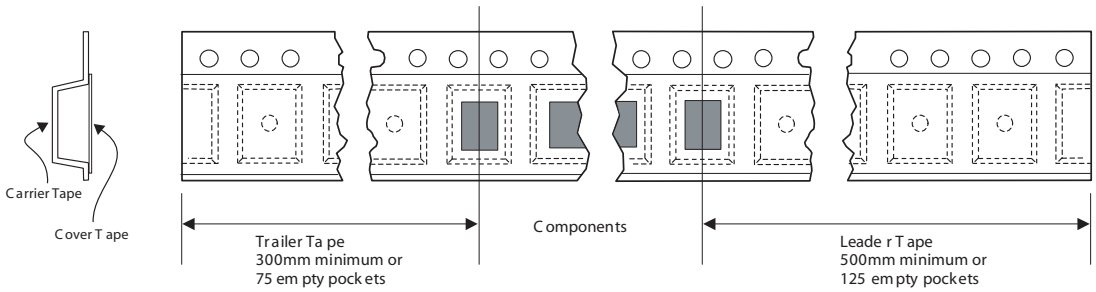


193mm x 183mm x 80mm
Pizza Box for Standard Option

Barcode Label sample

XH1 MT2306ACTR
XH2 C97I27K1-068I-K133 M13274
QTY: 3000
SPEC :
MOS-TECH SEMICONDUCTOR LTD (ACTR)

SOT23-3L Tape Leader and Trailer
Configuration: Figure 2.0



SOT-23 Std Tape and Reel Data, continued

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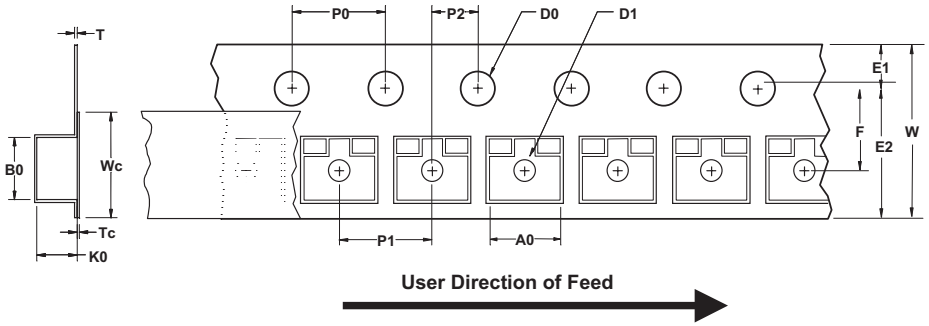
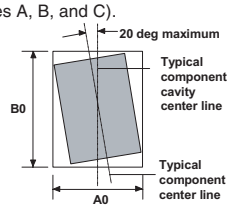
SOT23-3L Embossed Carrier Tape
Configuration: Figure 3.0



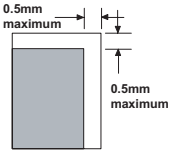
Dimensions are in millimeter														
Pkg type	**A0**	**B0**	**W**	**D0**	**D1**	**E1**	**E2**	**F**	**P1**	**P0**	**K0**	**T**	**Wc**	**Tc**
SOT-23 (8mm)	3.15 +/-0.10	2.77 +/-0.10	8.0 +/-0.3	1.55 +/-0.05	1.125 +/-0.125	1.75 +/-0.10	6.25 min	3.50 +/-0.05	4.0 +/-0.1	4.0 +/-0.1	1.30 +/-0.10	0.228 +/-0.013	5.2 +/-0.3	0.06 +/-0.02

Notes: A0, B0, and K0 dimensions are determined with respect to the EIA/Jedec RS-481 rotational and lateral movement requirements (see sketches A, B, and C).

Sketch A (Side or Front Sectional View)
Component Rotation

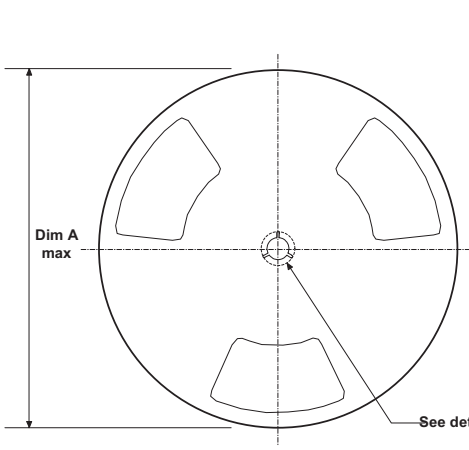


Sketch B (Top View)
Component Rotation

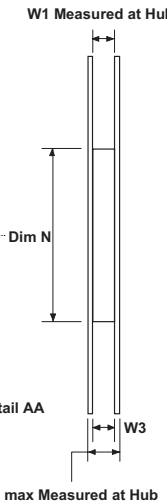


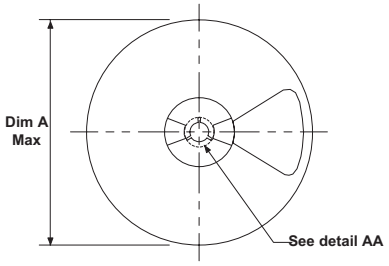
Sketch C (Top View)
Component lateral movement

SOT23-3L Reel Configuration: Figure 4.0

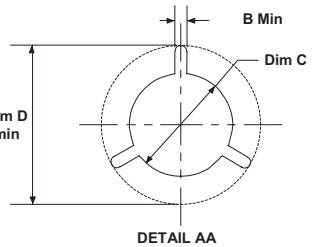


13" Diameter Option





7" Diameter Option



Dimensions are in inches and millimeters									
Tape Size	**Reel Option**	**Dim A**	**Dim B**	**Dim C**	**Dim D**	**Dim N**	**Dim W1**	**Dim W2**	**Dim W3 (LSL-USL)**
8mm	7" Dia	7.00 177.8	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	2.165 55	0.331 +0.059/-0.000 8.4 +1.5/0	0.567 14.4	0.311 - 0.429 7.9 - 10. 9
8mm	13" Dia	13.00 330	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	4.00 100	0.331 +0.059/-0.000 8.4 +1.5/0	0.567 14.4	0.311 - 0.429 7.9 - 10. 9

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Keep safety first in your circuit designs!

1. MOS-TECH Semiconductor Corp. puts the maximum effort into making semiconductor products better and more reliable, but there is always the possibility that trouble may occur with them. Trouble with semiconductors may lead to personal injury, fire or property damage.
   Remember to give due consideration to safety when making your circuit designs, with appropriate measures such as (i) placement of substitutive, auxiliary circuits, (ii) use of nonflammable material or (iii) prevention against any malfunction or mishap.